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circuits. In addition, in contrast to the present application, which used the MOS capacitor provided between the power source wire and the ground potential wire as the element subjected to protection against electrostatic breakdown, the conventional techniques make use of the gate of the MOS transistor located in between the input/output terminals and the ground potential wire.

Page 19, please delete the first full paragraph and replace it with the following paragraph:

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When the discharge test switch 2 is turned on after the semiconductor integrated circuit device according to the first embodiment is subjected to electrification, the charge charged in the capacitance held by the ground potential wire 12 from the ground terminal 14 is discharged to the ground. At this time, the voltage between both terminals of the MOS capacitor is clamped at a voltage lower than the dielectric breakdown voltage by the electrostatic protection element 18. Thus, the MOS capacitor is protected from the electrostatic breakdown.

IN THE CLAIMS:

Please enter the following amended claims:

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1. (Amended) A semiconductor integrated circuit device comprising:
a MOS capacitor, one end of which is connected to a power source wire for supplying a power source voltage, and another end of which is connected to a ground potential wire for supplying a ground potential;
a ground terminal, to which said ground potential wire is connected; and